

10/562869

IAP15 Rec'd PCT/PTO 28 DEC 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No. :

U.S. National Serial No. :

Filed :

PCT International Application No. : PCT/DE2004/001376

VERIFICATION OF A TRANSLATION

I, the below named translator, hereby declare that:

My name and post office address are as stated below;

That I am knowledgeable in the German language in which the below identified international application was filed, and that, to the best of my knowledge and belief, the English translation of the amended sheets of the international application No. PCT/DE2004/001376 is a true and complete translation of the amended sheets of the above identified international application as filed.

I hereby declare that all the statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the patent application issued thereon.

Date: December 16, 2005



Full name of the translator : Michael Amos WHITTAKER

For and on behalf of RWS Group Ltd

Post Office Address : Europa House, Marsham Way,
Gerrards Cross, Buckinghamshire,
England.

10/562869

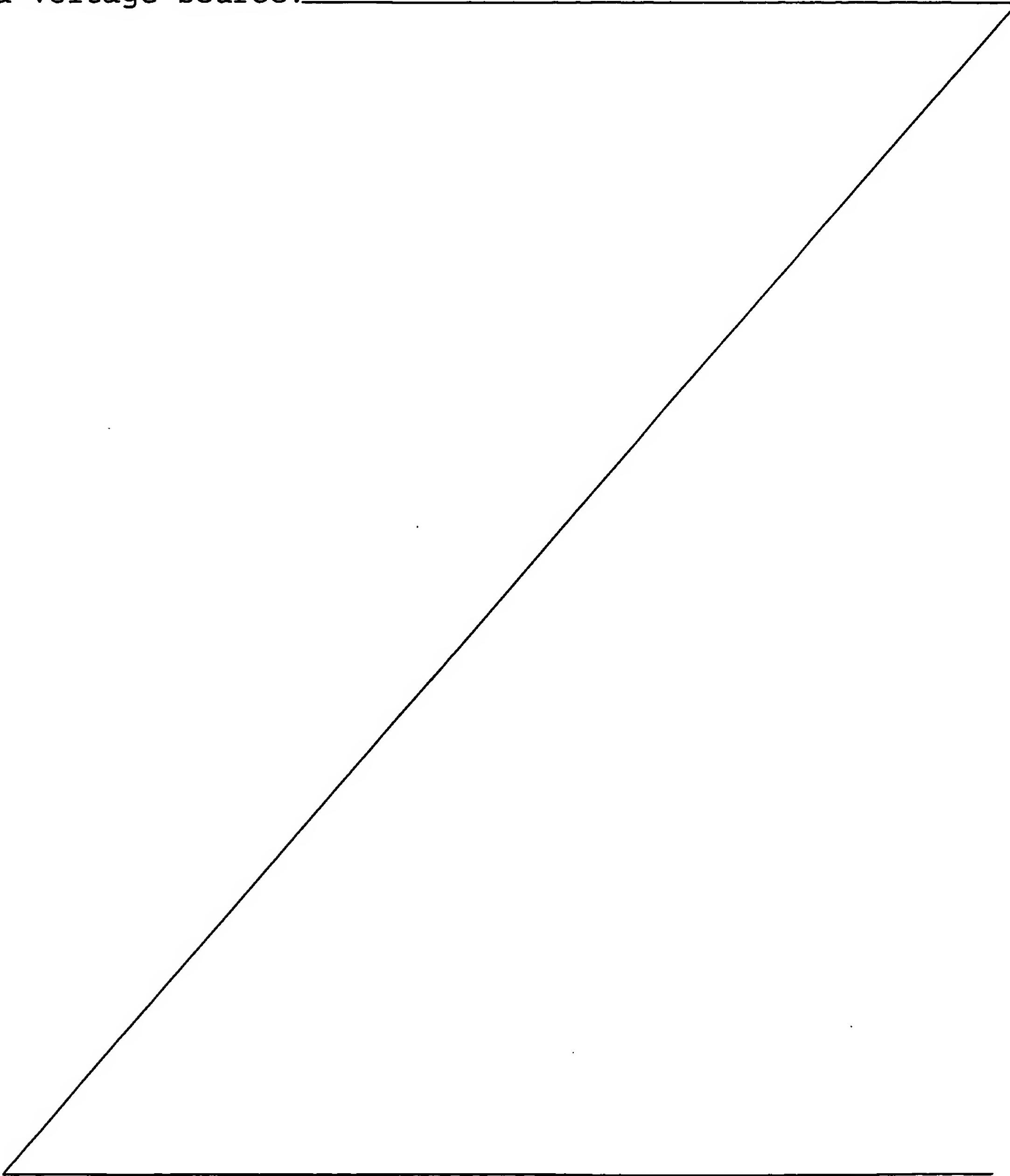
JAP15 Rec'd PCT/PTO 28 DEC 2005

PCT/DE2004/001376

T/46451WO

New Claim 1:

1. An organic logic gate comprising at least one charging field effect transistor (charging FET) and at least one switching field effect transistor (switching FET), the charging FET having at least one gate electrode, a source electrode and a drain electrode, characterized in that the gate electrode of the charging FET is not connected via an electrical line to a voltage source.



T/46451WO

PCT/DE2004/001376

Neuer Anspruch 1:

1. Organisches Logikgatter mit mindestens einem Lade-Feldeffekttransistor (Lade-FET) und mindestens einem Schalt-Feldeffekttransistor (Schalt-FET), wobei der Lade-FET mindestens eine Gate-Elektrode, eine Source-Elektrode und eine Drain-Elektrode aufweist, dadurch gekennzeichnet, dass die Gate-Elektrode des Lade-FETs nicht über eine elektrische Leitung mit einer Spannungsquelle verbunden ist.

